

PATENT
Attorney Docket No. 14912.786

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application	PATENT APPLICATION MAY ECELYA
Inventor(s): Stephen E. Savas) Art Unit: 1763
Application No.: 10/053,138) Examiner: Parviz Hassanzadeh
Filed: 01/18/2002)
Title: Pulsed Plasma Processing of Semiconductor Substrates))

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR §1.97

Commissioner for Patents Washington, D.C. 20231

Sir:

Listed on an attached Form PTO-1449 is information known to applicant(s). The references listed on Form PTO-1449 were cited in U.S. patent 6,253,704 of which the present application is a continuation and/or U.S. patent 5,983,828 of which U.S. patent 6,253,704 is a divisional. A copy of each listed publication and U.S. and foreign patent is available to the Examiner in parent application no. 09/398,553 now issued as U.S. patent 6,523,704 and/or application no. 08/727,209 now issued as U.S. patent 5,983,828. Applicant will supply a copy of any cited document(s) upon request by the Examiner.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP §609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in \$1.56.

iiic sta	terrer i	3, 01 13 0	considered to be, material to patentability as defined in §1.50.
\boxtimes	This st	tatement	qualifies under 37 CFR §1.97, subsection (b) because (check all that apply):
	\boxtimes	(1)	It is being filed within 3 months of the application filing date and is other than a continued prosecution application under § 1.53(d) OR
		(2)	It is being filed within 3 months of entry of a national stage OR
	\boxtimes	(3)	It is being filed before the mail date of the first Office Action on the merits OR
		(4)	It is being filed before the mailing of a first Office Action after the filing of a request for continued examination under § 1.114

Attorney Docket No.: 14912.786

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	date of forth in merits,	a national application; (2) three months beyon §1.491 in an international application; or (3)	ter the latest of: (1) three months beyond the filing ond the date of entry of the national stage as set) the mailing date of a first Office action on the a final office action under §1.113 or a notice of
		a certification as specified in §1.97(e) is pro	ovided below; or
		a fee of \$180.00 as set forth in §1.17(p) is a payment of other papers filed together with	nuthorized below, enclosed, or included with the this statement.
			ter the mailing date of the earlier of a final office §1.311, but before payment of the issue fee, then:
	A.	a certification as specified in §1.97(e) is con	mpleted below; and
	B.	a petition under 37 CFR §1.97(d) requesting herewith; and	g consideration of this statement is submitted
	C.	a fee of \$130.00 as set forth in \$1.17(i)(1) i payment of other papers filed together with	s authorized below, enclosed, or included with the this statement.
	\$ <u>0</u>		athorized to charge the above-referenced fees of voverpayment associated with this communication 2.786).
		Re	espectfully submitted,
		w	ILSON SONSINI GOODRICH & ROSATI
Dated:		5-20-63 By	y:

650 Page Mill Road Palo Alto, CA 94304-1050 (650) 493-9300 Customer No. 021971

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)763 PTO/SB/21 (6-99)

Piease type a plus sign (+) inside this box → Approved for use through 09/30/2000. OMB 0651-0031 Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number. 10/053,138 Application Number **TRANSMITTAL** 01/18/2002 Filing Date **FORM** Savas First Named Inventor to be used for all correspondence after initial filing) 1763 Group/Art Unit Parviz Hassanzad **Examiner Name** Total Number of Pages in This Submission 1.086 Attorney Docket Number 14912.786 ENCLOSURES (check all that apply) Assignment Papers After Allowance Communication Fee Transmittal Form (for an Application) to Group Appeal Communication to Board Fee Attached Drawing(s) of Appeals and Interferences Appeal Communication to Group Amendment / Response Licensing-related Papers (Appeal Notice, Brief, Reply Brief) After Final Petition Routing Slip (PTO/SB/69) **Proprietary Information** and Accompanying Petition Version with Markings Showing Petition to Convert to a Status Letter Changes Provisional Application Additional Enclosure(s) Affidavits/declaration(s) Power of Attorney, Revocation (please identify below): Change of Correspondence Address Extension of Time Request Terminal Disclaimer Information Disclosure Statement Small Entity Statement Certified Copy of Priority Request for Refund Document(s) Response to Missing Parts/ Remarks Incomplete Application Response to Missing Parts under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY OR AGENT Firm Michael J. Murphy, Reg. No. 37,404, WILSON SONSINI GOODRICH & ROSATI Individual name Signature Date 021971 Customer Number: 10-03 CERTIFICATE OF FACSIMILE TRANSMISSION MAILING I hereby certify that this correspondence is being transmitted to the Commissioner for Patents, Washington, D.C. 20231, on this date: MAY 29 2003 EV 333492819 US

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Date

Typed or printed name

Signature

Linda Faye



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INFORM			ATTY. DOCKET NO.	SE	RIAL NO.	10	×.
CITATION 1		14912.786	10/	053,138	MALECY		
	PTO-1449		APPLICANT Stephen E. Sa	avas	Ga	Z KE	
	110-1449		FILING DATE 01/18/2002	GR	SERIAL NO. 10/053,138 GROUP 1763		7003
		U.S	S. PATENT DOCUMENTS				700
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING	G DATE
	5,571,366	11/1996	Ishii et al.	156	345		
	5,647,913	07/1992	Blalock	118	723I		
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	6,068,784	05/2000	Collins et al.	118	723I		
		FOR	EIGN PATENT DOCUMENTS	S		,I	
EXAMINER'S	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	SLATION
INITIALS						YES	NO
	2 105 729 A	30.03.83	Great Britain	C08 J7/00	C08F 2/52		
	408288272	11/1996	Japan	C23C	16/50		
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	2240114A	07/1991	Great Britain	C23C	16/26		
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	R.W. Boswell e	t al., "Pulsed l	nigh rate plasma etching with vari	iable Si/SiO	selectivity and	variable S	Si etch
			(10), 15 Nov. 1985, pp. 1095-10		D'' T' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '	-	
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			ociety Proceedings, Vol. 93-21, 19				· · · -
	PCT International Search Report dated 07 MAR 1997 of corresponding PCT Application No. PCT/US96/16138, references cited above.						
	PC1/US96/161	38, references					
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		U.S.	PATENT DOCUMENT						
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLA	SUBCLASS	FILING	FILING DATE		
	5,811,022	09/22/1998	Savas et al.	216	68	11/15/19	994		
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	5,419,805	05/30/1995	Jolly	156	643.1	02/18/19	994		
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	5,332,441	07/26/1994	Barnes et al.	118	723	10/31/19	991		
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	OTHER DO	CUMENTS (I	ncluding Author, Title, Dat	te, Pertinen	t Pages, Etc.)				
			measurements and etching in			oupled	-		
	plasma in chlor	ine," Plasma So	urces Sci. Technol. 5, p. 139	(1996).					
	C. Charles et al	, "Breakdown,	steady-state, and decay regim	nes in pulse	d oxygen helicon	diffusion			
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10/055,138 May ECE TO S APPLICANT Stephen E. Savas PTO-1449 FILING DATE 01/18/2002 **U.S. PATENT DOCUMENTS CLASS SUBCLASS** FILING DATE **EXAMINER'S** PATENT NO. DATE NAME INITIALS 06/07/1994 10/20/1992 5,318,668 Tamaki et al. 156 662 5,318,664 06/07/1994 Saia et al. 156 643 11/14/1991 05/17/1994 Kadomura 156 662 05/29/1992 5,312,518 5,310,452 05/10/1994 Doki et al. 643 07/20/1992 156 492.21 5,289,010 02/22/1994 Shohet 250 12/08/1992 5,286,344 02/15/1994 Blalock et al. 156 657 06/15/1992 5,286,297 02/15/1994 Moslehi et al. 118 723 E 06/24/1992 5,284,549 02/08/1994 Barnes et al. 156 662 01/02/1992 5,259,924 11/09/1993 Mathews et al. 156 653 04/08/1992 FOREIGN PATENT DOCUMENTS TRANSLATION EXAMINER'S PATENT NO. DATE COUNTRY **CLASS SUBCLASS INITIALS** YES NO \Box П П П OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) X. Chen et al., "Pulse plasma polymerization of tetramethyltin: Nanoscale compositional control of film chemistry," Chem. Mater. 8, p. 1067 (1996). K. Hashimoto et al., "Reduction of the charging damage from electron shading," 1996 1st International Symposium on Plasma Process-Induced Damage, Santa Clara, CA, May 13-14 (1996). M.A. Lieberman et al., "Global models of pulse-power-modulated high density, low pressure discharges," Plasma Sources Sci. Technol. 5, p. 145 (1996). **EXAMINER** DATE CONSIDERED

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GROUP 1200 ATTY. DOCKET NO. SERIAL NO. INFORMATION DISCLOSURE 14912.786 10/053,138 **CITATION** APPLICANT Stephen E. Savas PTO-1449 **GROUP 1763** FILING DATE 01/18/2002 **U.S. PATENT DOCUMENTS** PATENT NO. DATE NAME **CLASS SUBCLASS** FILING DATE **EXAMINER'S INITIALS** 09/07/1993 156 643 01/29/1992 5,242,538 Hamrah et al. 5,234,529 08/10/1993 Johnson 156 345 10/10/1991 225 5,231,057 07/27/1993 Doki et al. 437 08/20/1991 07/13/1993 Westmoreland 437 174 02/10/1992 5,227,331 06/15/1993 252 79.3 10/17/1991 5,219,485 Wang et al. 5,217,567 06/08/1993 Cote et al. 156 643 02/27/1992 156 5,201,994 04/13/1993 Nonaka et al. 643 11/17/1989 5,188,704 02/23/1993 Babie et al. 156 643 05/09/1991 5,160,408 11/03/1992 Long 156 656 04/27/1990 FOREIGN PATENT DOCUMENTS TRANSLATION **EXAMINER'S** PATENT NO. DATE **COUNTRY CLASS SUBCLASS INITIALS** YES NO \Box $\overline{}$ OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Y. Lin et al., "Negative and positive ions from CF₄/O₂ RF discharges in etching Si," Appl. Phys. Lett. 62, p. 675 (1992). M. Moisan et al., "Radio frequency or microwave plasma reactors? Factors determining the optimum

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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GROUP 12003 SERIAL NO. ATTY. DOCKET NO. INFORMATION DISCLOSURE 10/053,138 14912.786 **CITATION** APPLICANT Stephen E. Savas PTO-1449 FILING DATE 01/18/2002 **GROUP 1763 U.S. PATENT DOCUMENTS SUBCLASS** FILING DATE **EXAMINER'S** PATENT NO. DATE NAME **CLASS INITIALS** 10/06/1992 551 01/03/1991 5,153,442 Bovino et al. 250 05/12/1992 156 643 11/29/1989 5,112,435 Wang et al. 156 643 5,108,542 04/28/1992 Lin 08/23/1990 04/16/1991 156 643 07/11/1988 5,007,982 Tsou 4,994,715 02/19/1991 Asmus et al. 315 111.71 07/21/1988 437 110 02/12/1988 4,933,300 06/12/1990 Koinuma et al. 4,985,112 01/15/1991 Egitto et al. 156 643 02/09/1987 4,970,435 11/13/1990 Tanaka et al. 315 111.21 12/08/1988 06/26/1986 4,935,661 06/19/1990 Heinecke et al. 313 231.31 FOREIGN PATENT DOCUMENTS TRANSLATION **SUBCLASS** COUNTRY **CLASS EXAMINER'S** PATENT NO. DATE **INITIALS** YES NO \Box OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) L.J. Overzet et al., "Enhancement of the negative ion flux to surfaces from radio-frequency processing discharges," J. Appl. Phys. 66, p. 1622 (1989). L.J. Overzet, "Model for charge movement after the radio frequency excitation is extinguished," J. Vac. Sci. Technol. A11, p. 1114 (1993).

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APPLICANT Stephen E. Savas

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	4,897,365	01/30/1990	Baldi et al.	437	69	11/23/1	987
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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	-	LATION
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			Including Author, Title, Date, P				
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GROUP 1700 APPLICANT Stephen E. Savas PTO-1449 **GROUP 1763** FILING DATE 01/18/2002 **U.S. PATENT DOCUMENTS EXAMINER'S** PATENT NO. DATE **NAME CLASS SUBCLASS FILING DATE INITIALS** 03/20/1987 156 643 4,793,897 12/27/1988 Dunfield et al. 427 39 12/10/1985 4,749,589 06/07/1988 Heinecke et al. 4,734,157 03/29/1988 Carbaugh et al. 156 643 03/18/1987 Dieleman et al. 10/31/1983 4,717,447 01/05/1988 156 643 204 192.22 02/14/1986 4,693,805 09/15/1987 Quazi 4,654,114 03/31/1987 Kadomura 156 643 12/16/1985 156 643 03/04/1985 4,585,516 04/29/1986 Corn et al. 40 427 4,568,563 02/04/1986 Jackson et al. 06/21/1985 4,263,088 04/21/1981 Gorin 156 626 06/25/1979 FOREIGN PATENT DOCUMENTS TRANSLATION **SUBCLASS EXAMINER'S** PATENT NO. DATE COUNTRY **CLASS INITIALS** YES NO \Box П OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) S. Samukawa, "Pulse time-modulated electron cyclotron resonance plasma etching with low radio-frequency substrate bias," Appl. Phys. Lett. 68, p. 316 (1996). S. Samukawa et al., "Time-modulated electron cyclotron resonance plasma discharge for controlling generation of reactive species," Appl. Phys. Lett. 63, p. 2044 (1993). S. Samukawa et al., "Pulse-time modulated electron cyclotron resonance plasma etching for highly selective, highly anisotropic, and notch-free polycrystalline silicon patterning," J. Vac. Sci. Technol. B12, p. 3300 (1994). **EXAMINER DATE CONSIDERED**

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APPLICANT Stephen E. Savas

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANS	SLATION
INITIALS						YES	NO
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